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FDD4243
40V P-Channel PowerTrench® MOSFET
-40V, -14A, 44mΩ

Features

■ Max $r_{DS(on)}$ = 44mΩ at V_{GS} = -10V, I_D = -6.7A

■ Max $r_{DS(on)}$ = 64mΩ at V_{GS} = -4.5V, I_D = -5.5A

■ High performance trench technology for extremely low $r_{DS(on)}$

■ RoHS Compliant

General Description

This P-Channel MOSFET has been produced using Fairchild Semiconductor's proprietary PowerTrench® technology to deliver low $r_{DS(on)}$ and optimized Bvdss capability to offer superior performance benefit in the applications.

Application

■ Inverter
■ Power Supplies

D-PAK (TO-252)
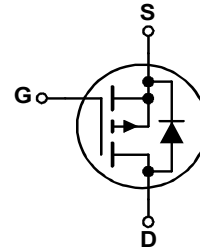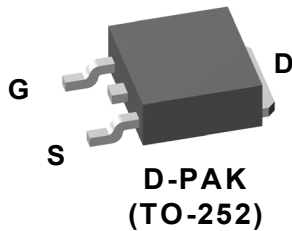
MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			-40	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous (Package limited)	T_C= 25°C		-14	A
	-Continuous (Silicon limited)	T_C= 25°C	(Note 1)	-24	
	-Continuous	T_A= 25°C	(Note 1a)	-6.7	
	-Pulsed			-60	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	84	mJ
P_D	Power Dissipation	T_C= 25°C		42	W
	Power Dissipation		(Note 1a)	3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case			3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		(Note 1a)	40	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD4243	FDD4243	D-PAK(TO-252)	13"	16mm	2500 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = -250µA, V_{GS} = 0V	-40			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = -250µA, referenced to 25°C		-32		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -32V, V_{GS} = 0V			-1	µA
		T_J = 125°C			-100	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = -250µA	-1.4	-1.6	-3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250µA, referenced to 25°C		4.7		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = -10V, I_D = -6.7A		36	44	mΩ
		V_{GS} = -4.5V, I_D = -5.5A		48	64	
		V_{GS} = -10V, I_D = -6.7A, T_J = 125°C		53	69	
g_{FS}	Forward Transconductance	V_{DS} = -5V, I_D = -6.7A		16		S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	V_{DS} = -20V, V_{GS} = 0V, f = 1MHz		1165	1550	pF
C_{oss}	Output Capacitance			165	220	pF
C_{rss}	Reverse Transfer Capacitance			90	135	pF
R_g	Gate Resistance	f = 1MHz		4		Ω

Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = -20V, I_D = -6.7A, V_{GS} = -10V, R_{GEN} = 6Ω		6	12	ns
t_r	Rise Time			15	26	ns
$t_{d(off)}$	Turn-Off Delay Time			22	35	ns
t_f	Fall Time			7	14	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V	V_{DD} = -20V, I_D = -6.7A, V_{GS} = -10V		21	29	nC
Q_{gs}	Gate to Source Gate Charge			3.4		nC
Q_{gd}	Gate to Drain "Miller" Charge			4		nC

Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = -6.7A (Note 2)		0.86	1.2	V
t_{rr}	Reverse Recovery Time	I_F = -6.7A, di/dt = 100A/µs		29	43	ns
Q_{rr}	Reverse Recovery Charge			30	44	nC

Notes:

1: $R_{\theta JA}$ is sum of junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JC}$ is determined by the user's board design.

a. 40°C/W when mounted on a 1 in^2 pad of 2 oz copper

b. 96°C/W when mounted on a minimum pad.

2: Pulse Test: Pulse Width < 300µs, Duty cycle < 2.0%.
3: Starting T_J = 25°C, L = 3mH, I_{AS} = 7.5A, V_{DD} = 40V, V_{GS} = 10V.

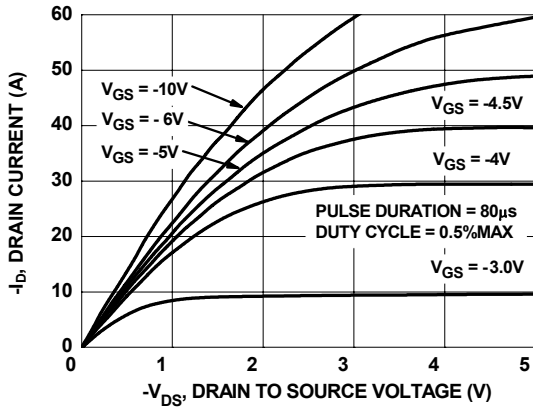## Typical Characteristics T_J = 25°C unless otherwise noted
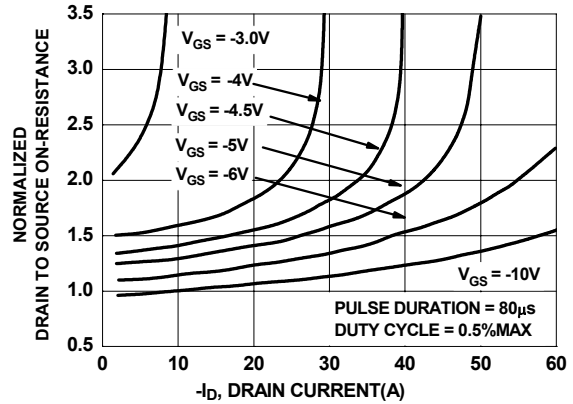

Figure 1. On Region Characteristics

**Figure 2. Normalized On-Resistance
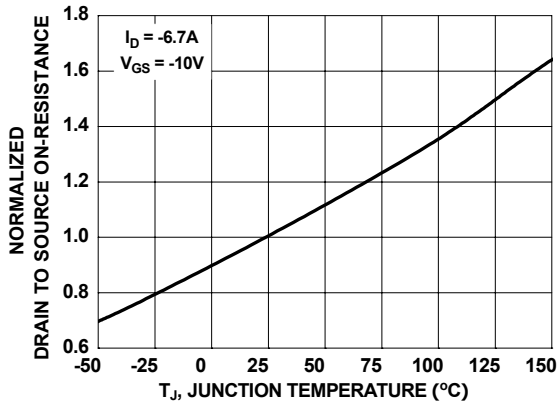vs Drain Current and Gate Voltage**

**Figure 3. Normalized On Resistance
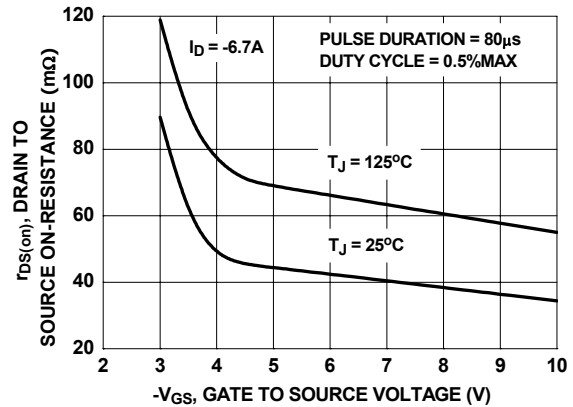vs Junction Temperature**
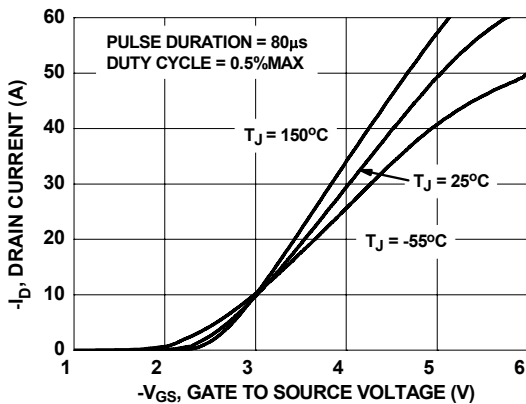

**Figure 4. On-Resistance vs Gate to
Source Voltage**
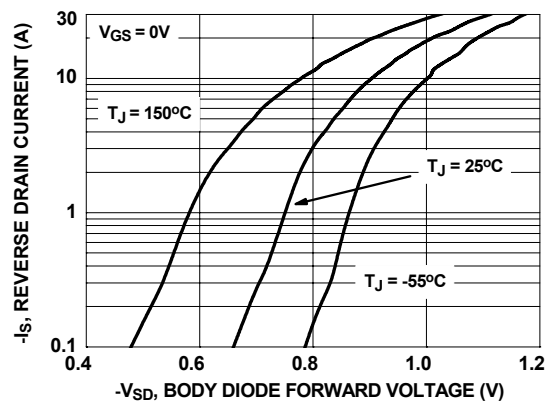

Figure 5. Transfer Characteristics

**Figure 6. Source to Drain Diode
Forward Voltage vs Source Current**
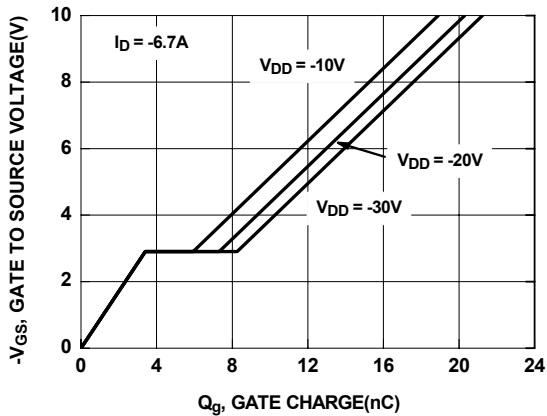
Typical Characteristics T_J = 25°C unless otherwise noted

Figure 7. Gate Charge Characteristics
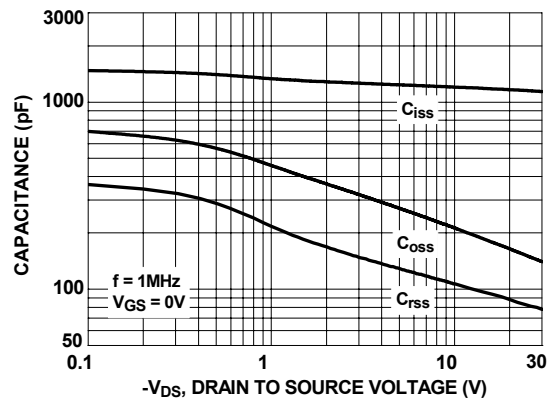
Figure 8. Capacitance vs Drain to Source Voltage
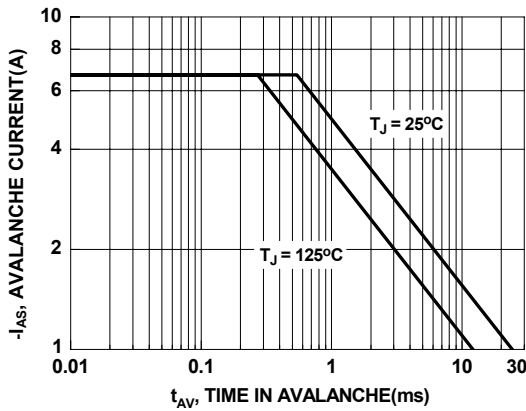
Figure 9. Unclamped Inductive Switching Capability
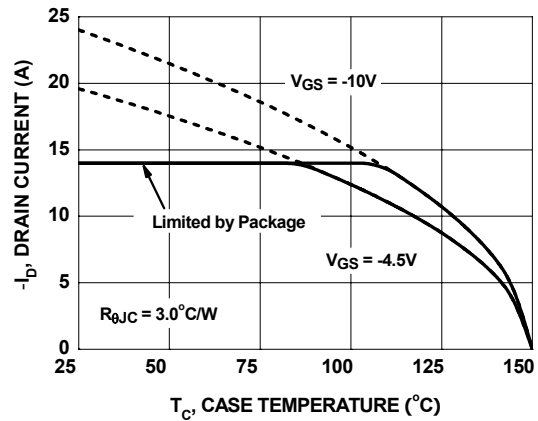
Figure 10. Maximum Continuous Drain Current vs Case Temperature
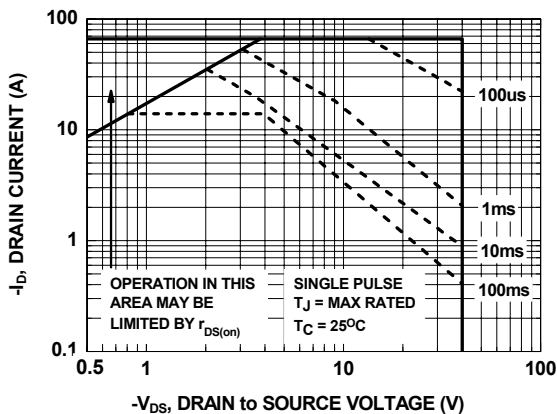
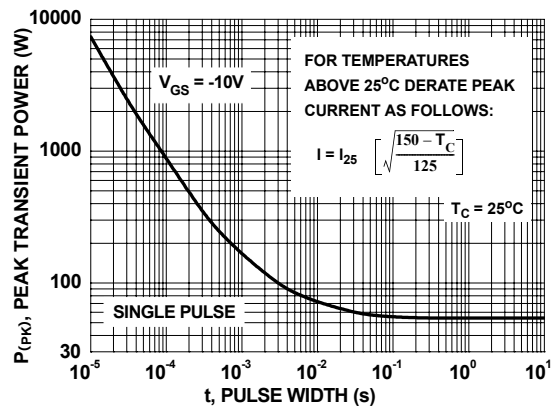Figure 11. Forward Bias Safe Operating Area

Figure 12. Single Pulse Maximum Power Dissipation

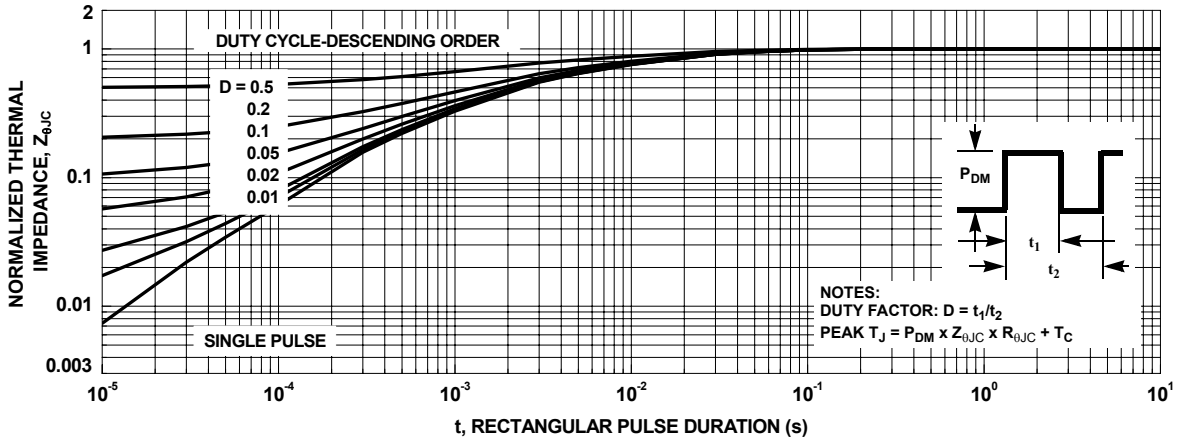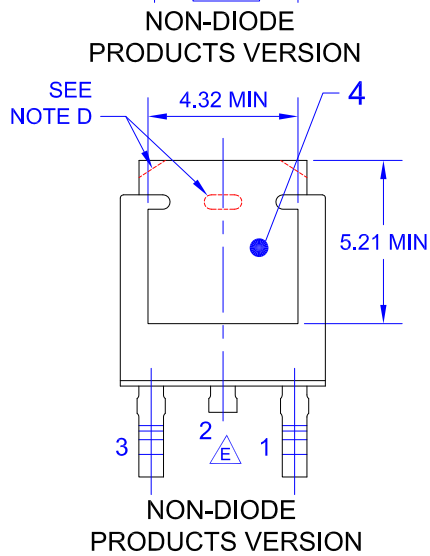**Typical Characteristics** T_J = 25°C unless otherwise noted

NORMALIZED THERMAL IMPEDANCE, $Z_{\theta JC}$

DUTY CYCLE-DESCENDING ORDER

D = 0.5
0.2
0.1
0.05
0.02
0.01

SINGLE PULSE

P_{DM}

t_1

t_2

NOTES:
DUTY FACTOR: D = t_1/t_2
PEAK T_J = P_{DM} x $Z_{\theta JC}$ x $R_{\theta JC}$ + T_C

t, RECTANGULAR PULSE DURATION (s)

Figure 13. Transient Thermal Response Curve

6.73
6.35

[A]

5.46
5.21

1.27
0.89

6.22
5.97

[E]
1.02 MAX

[C]

0.25 MAX

1   2   3

ISOLATED PLASTIC
BODY STUB

DIODE
PRODUCTS VERSION

(0.59)

1.14
0.76

0.89
0.64

| ⌖ | 0.25 Ⓜ | AⓂ | C |

2.29

4.57

NON-DIODE
PRODUCTS VERSION

5.55 MIN

4

6.50 MIN

6.40

2.85 MIN

1   3

1.25 MIN

2.28

4.56

LAND PATTERN
RECOMMENDATION

SEE
NOTE D

4.32 MIN

4

5.21 MIN

3   2 [E] 1

NON-DIODE
PRODUCTS VERSION

3   2   1

DIODE
PRODUCTS VERSION

[B]

2.39
2.18

0.58
0.45

10.41
9.40

SEE DETAIL A

| ⌓ | 0.10 | B |

GAGE PLANE

0.61
0.45

10°
0°

1.78
1.40

(2.90)

0.51

(1.54)

0.127 MAX

SEATING PLANE

DETAIL A
(ROTATED -90°)
SCALE: 12X

NOTES: UNLESS OTHERWISE SPECIFIED
A) THIS PACKAGE CONFORMS TO JEDEC, TO-252,
   ISSUE C, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER
   ASME Y14.5M-2009.
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED
   CORNERS OR EDGE PROTRUSION.
E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS
F) DIMENSIONS ARE EXCLUSIVE OF BURS,
   MOLD FLASH AND TIE BAR EXTRUSIONS.
G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD
   TO228P991X239-3N.
H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11

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PUBLICATION ORDERING INFORMATION

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